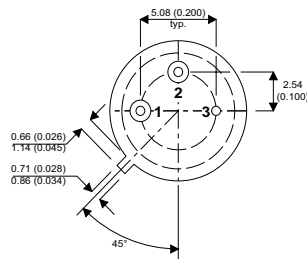
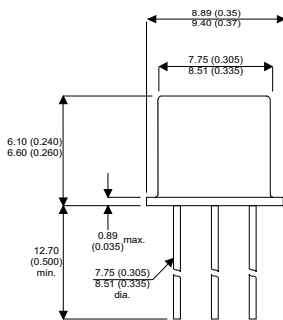


**MECHANICAL DATA**

Dimensions in mm (inches)


**TO39 – Package**

Pin 1 – Source    Pin 2 – Gate    Pin 3 – Drain

Also available in a low profile version.

**N-CHANNEL  
POWER MOSFET**
 **$BV_{DSS}$     500V**
 **$I_{D(cont)}$     1.5**
 **$R_{DS(on)}$     3.0 $\Omega$** 
**FEATURES**

- AVALANCHE ENERGY RATED
- HERMETICALLY SEALED
- DYNAMIC dv/dt RATING
- SIMPLE DRIVE REQUIREMENTS

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$V_{GS}$	Gate – Source Voltage	$\pm 20V$
$I_D$	Continuous Drain Current ( $V_{GS} = 10V$ , $T_{case} = 25^{\circ}C$ )	1.5A
$I_D$	Continuous Drain Current ( $V_{GS} = 10V$ , $T_{case} = 100^{\circ}C$ )	1A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	6.5A
$P_D$	Power Dissipation @ $T_{case} = 25^{\circ}C$	20W
	Linear Derating Factor	0.16W/ $^{\circ}C$
$E_{AS}$	Single Pulse Avalanche Energy <sup>2</sup>	0.11mJ
dv/dt	Peak Diode Recovery <sup>3</sup>	3.5V/ns
$T_J$ , $T_{stg}$	Operating and Storage Temperature Range	-55 to 150 $^{\circ}C$
$R_{\theta JC}$	Thermal Resistance Junction to Case	6.25 $^{\circ}C/W$
$R_{\theta JCA}$	Thermal Resistance Junction-to-Ambient	175 $^{\circ}C/W$

**Notes**

 1) Pulse Test: Pulse Width  $\leq 300\mu s$ ,  $\delta \leq 2\%$ 

 2) @  $V_{DD} = 50V$ ,  $L \geq 0.100mH$ ,  $R_G = 25\Omega$ , Peak  $I_L = 1.5A$ , Starting  $T_J = 25^{\circ}C$ 

 3) @  $I_{SD} \leq 1.5A$ ,  $di/dt \leq 50A/\mu s$ ,  $V_{DD} \leq BV_{DSS}$ ,  $T_J \leq 150^{\circ}C$ , SUGGESTED  $R_G = 7.5\Omega$

**ELECTRICAL CHARACTERISTICS** ( $T_{amb} = 25^{\circ}\text{C}$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>STATIC ELECTRICAL RATINGS</b>					
$BV_{DSS}$	Drain – Source Breakdown Voltage	$V_{GS} = 0$	$I_D = 1\text{mA}$	500	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	Reference to $25^{\circ}\text{C}$ $I_D = 1\text{mA}$		0.43	$\text{V}/^{\circ}\text{C}$
$R_{DS(on)}$	Static Drain – Source On–State Resistance	$V_{GS} = 10\text{V}$	$I_D = 1\text{A}$		3
		$V_{GS} = 10\text{V}$	$I_D = 1.5\text{A}$		3.45
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$	$I_D = 250\mu\text{A}$	2	4
$g_{fs}$	Forward Transconductance	$V_{DS} \geq 15\text{V}$	$I_{DS} = 1\text{A}$	1	$\text{S}(\bar{\omega})$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0$	$V_{DS} = 0.8BV_{DSS}$ $T_J = 125^{\circ}\text{C}$		25
					250
$I_{GSS}$	Forward Gate – Source Leakage	$V_{GS} = 20\text{V}$			100
$I_{GSS}$	Reverse Gate – Source Leakage	$V_{GS} = -20\text{V}$			-100
<b>DYNAMIC CHARACTERISTICS</b>					
$C_{iss}$	Input Capacitance	$V_{GS} = 0$			350
$C_{oss}$	Output Capacitance	$V_{DS} = 25\text{V}$			80
$C_{riss}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$			35
$Q_g$	Total Gate Charge	$V_{GS} = 10\text{V}$	$I_D = 1.5\text{A}$	7.3	16.7
$Q_{gs}$	Gate – Source Charge	$V_{DS} = 0.5BV_{DS}$			3
$Q_{gd}$	Gate – Drain (“Miller”) Charge	$I_D = 1.5\text{A}$		0.1	3
$t_{d(on)}$	Turn–On Delay Time	$V_{DS} = 0.5BV_{DS}$			8.7
$t_r$	Rise Time	$V_{DD} = 250\text{V}$			40
$t_{d(off)}$	Turn–Off Delay Time	$I_D = 1.5\text{A}$			30
$t_f$	Fall Time	$R_G = 7.5\Omega$			60
					30
<b>SOURCE – DRAIN DIODE CHARACTERISTICS</b>					
$I_S$	Continuous Source Current				1.5
$I_{SM}$	Pulse Source Current <sup>2</sup>				6.5
$V_{SD}$	Diode Forward Voltage	$I_S = 1.5\text{A}$	$T_J = 25^{\circ}\text{C}$		1.2
		$V_{GS} = 0$			
$t_{rr}$	Reverse Recovery Time	$I_F = 1.5\text{A}$	$T_J = 25^{\circ}\text{C}$		900
$Q_{rr}$	Reverse Recovery Charge	$d_i / d_t \leq 100\text{A}/\mu\text{s}$			5.9
		$V_{DD} \leq 50\text{V}$			
$t_{on}$	Forward Turn–On Time			Negligible	
<b>PACKAGE CHARACTERISTICS</b>					
$L_D$	Internal Drain Inductance (from centre of drain pad to die)			5.0	nH
$L_S$	Internal Source Inductance (from centre of source pad to end of source bond wire)			15.0	

**Notes**

- 1) Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ ,  $\delta \leq 2\%$
- 2) Repetitive Rating – Pulse width limited by maximum junction temperature.